

General Description:

The LWS60110H4 uses SGT technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. The package form is TO-252, which accords with the ROHS standard and Halogen Free standard.

Features:

- Fast Switching
- Low Gate Charge and $R_{DS(ON)}$
- Low Reverse transfer capacitances

Applications:

- DC-DC Converter
- Portable Equipment
- Power Management

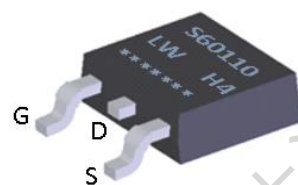
100% DVDS Tested

100% Avalanche Tested

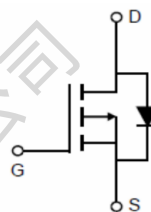


V_{DSS}	-60	V
I_D	-12	A
P_D	30	W
$R_{DS(ON)}$ TYPE	90	m Ω

Marking and Pin Assignment



Inner Equivalent Principium Chart



Package Marking and Ordering Information:

Marking	Part Number	Package	Packing	Qty.
S60110/LW H4/D.C.	LWS60110H4	TO-252	Reel	2500 Pcs

Absolute Maximum Ratings:

Symbol	Parameter	Value	Units
V_{DSS}	Drain-to-Source Voltage	-60	V
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$	-12
	Continuous Drain Current	$T_C=100^\circ\text{C}$	-7.6
I_{DM}^{al}	Pulsed Drain Current	-48	A
V_{GS}	Gate-to-Source Voltage	± 20	V
P_D	Power Dissipation	30	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	150, -55 to 150	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	260	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	4.17	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	50	$^\circ\text{C}/\text{W}$

Electrical Characteristic ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise specified):

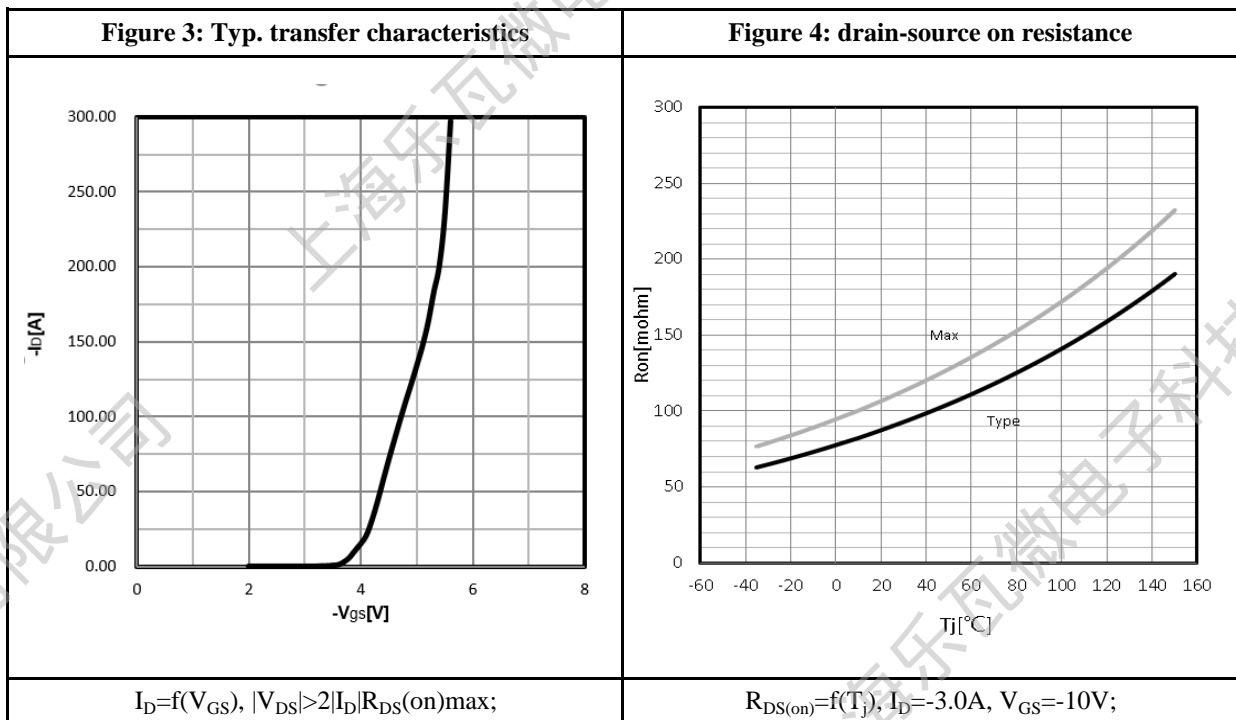
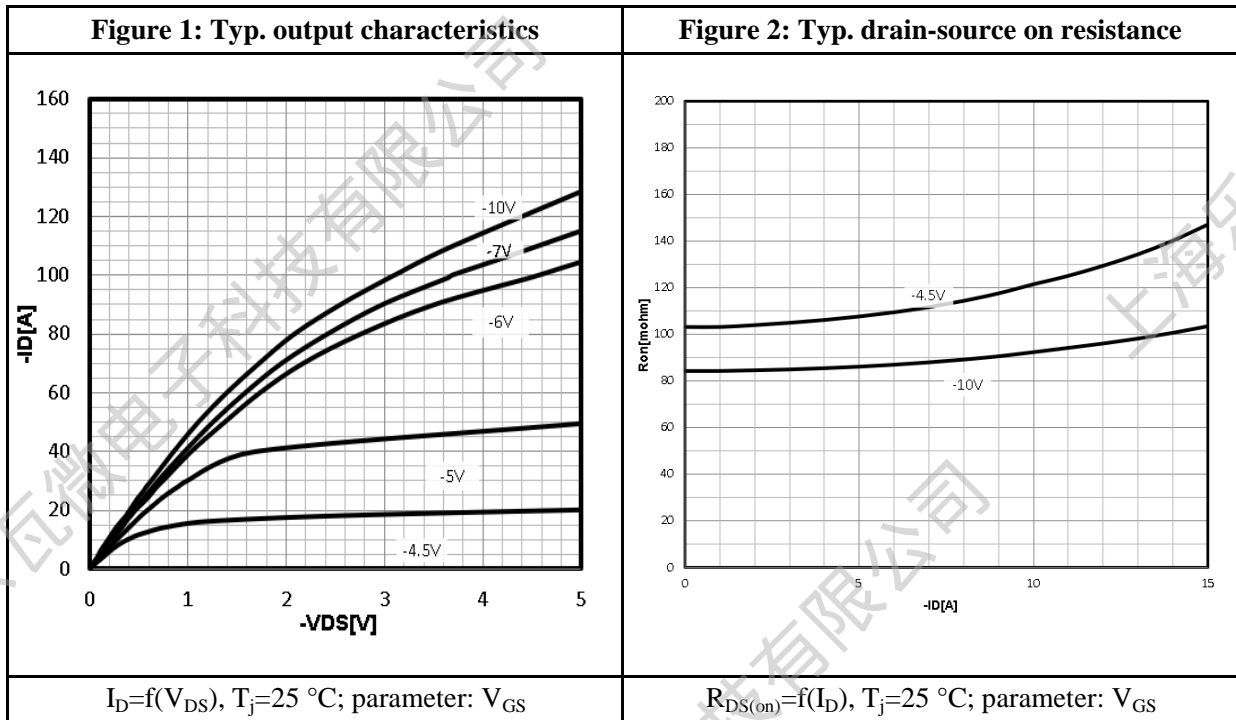
Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-60	--	--	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=-60V, V_{GS}=0V$	--	--	1.0	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=-20V, V_{DS}=0V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=+20V, V_{DS}=0V$	--	--	-100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-2.5	-3.0	-3.5	V
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=-10V, I_D=-3.0A$	--	90	110	m Ω

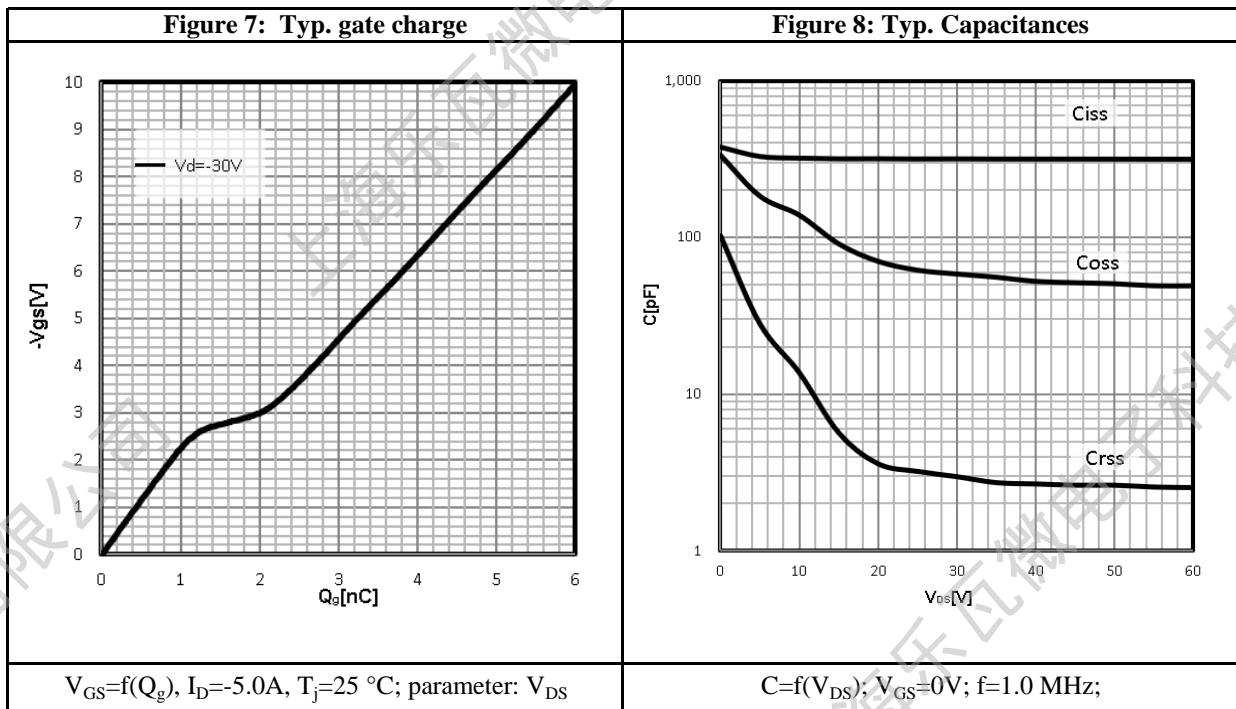
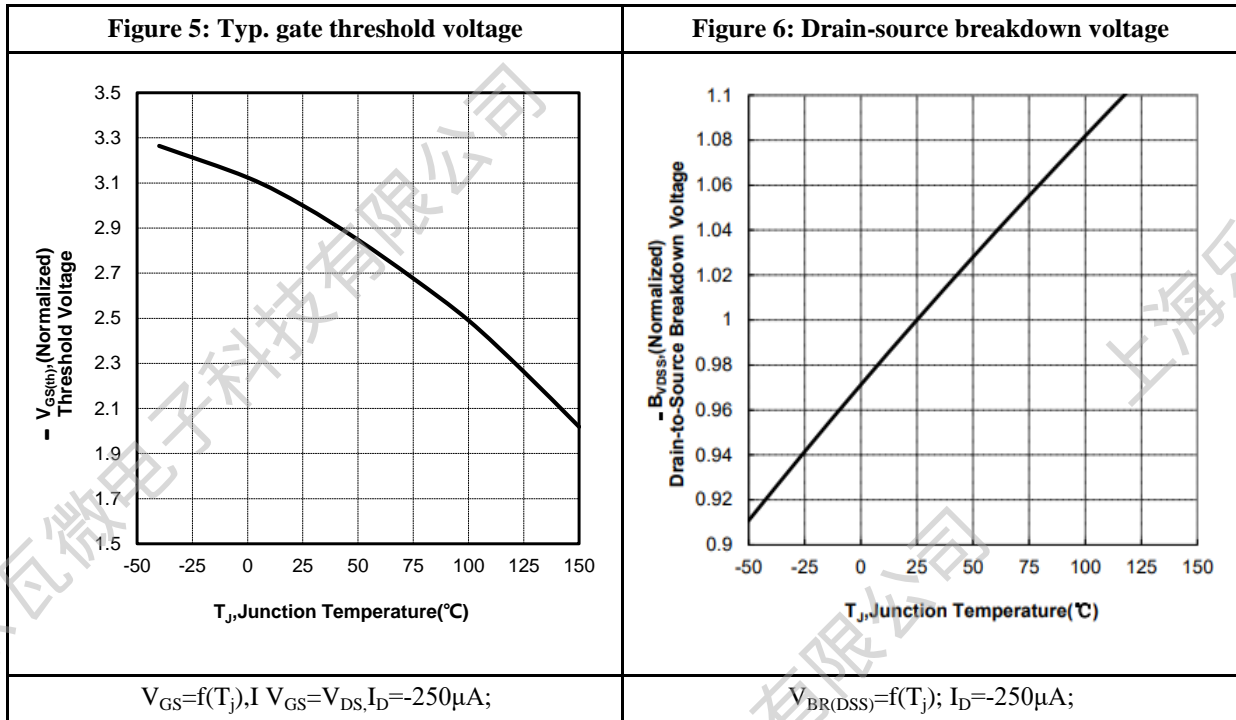
Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{GS} = 0V$	--	315	--	pF
C_{oss}	Output Capacitance	$V_{DS} = -30V$	--	58.6	--	
C_{rss}	Reverse Transfer Capacitance	$f = 1.0MHz$	--	2.98	--	

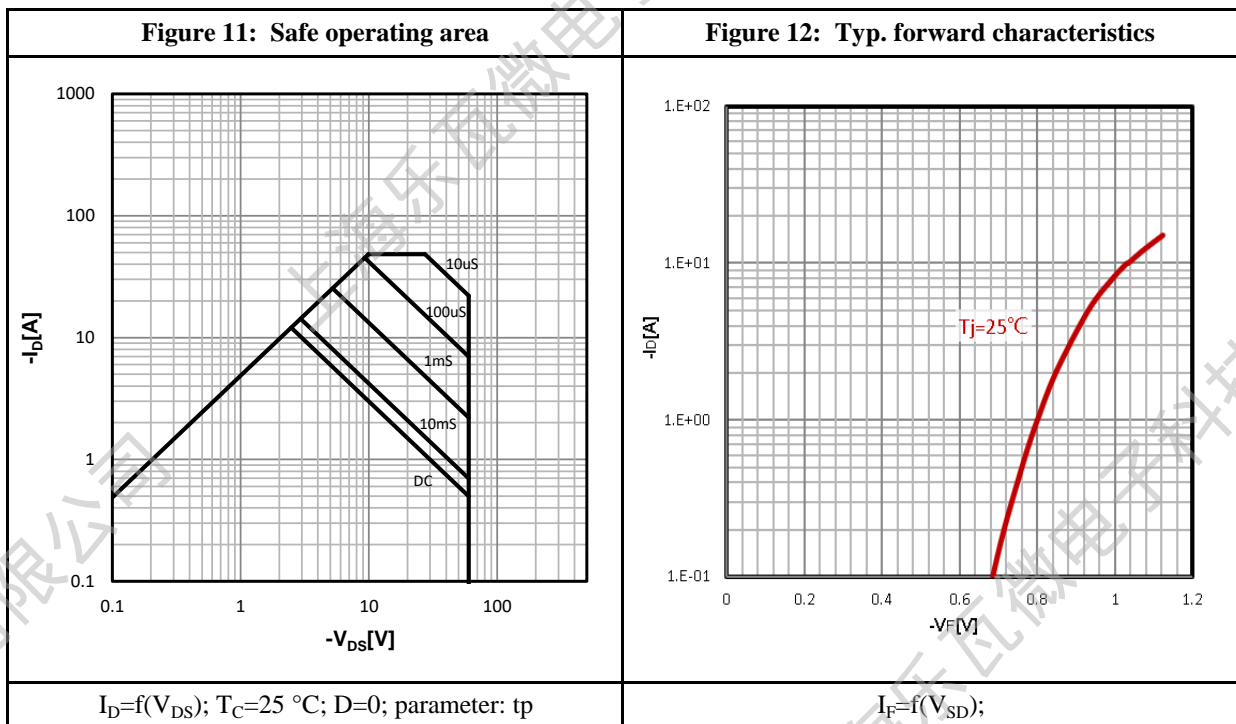
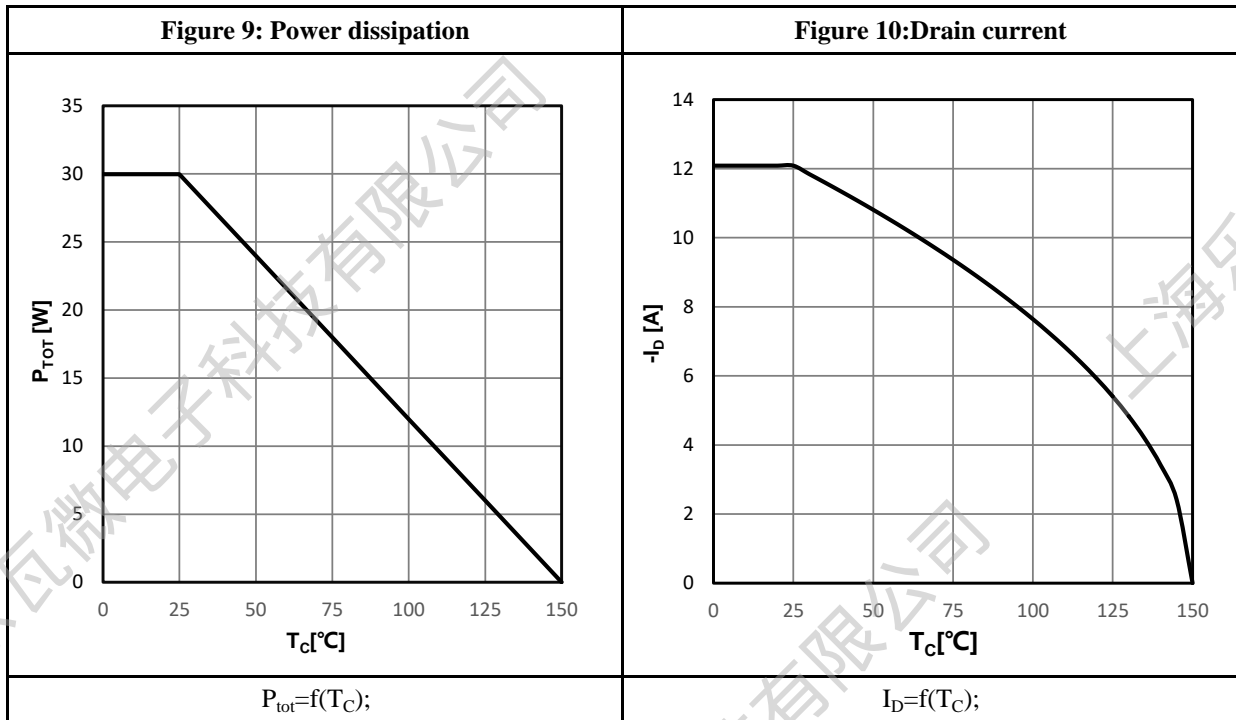
Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D = -2.0A$ $V_{DS} = -30V$ $V_{GS} = -10V$ $R_G = 5.0\Omega$	--	6.8	--	ns
t_r	Rise Time		--	8.0	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	16	--	
t_f	Fall Time		--	4.0	--	
Q_g	Total Gate Charge	$V_{GS} = -10V$	--	4.92	--	nC
Q_{gs}	Gate Source Charge	$V_{DS} = -30V$	--	0.97	--	
Q_{gd}	Gate Drain Charge	$I_D = -5.0A$	--	0.72	--	

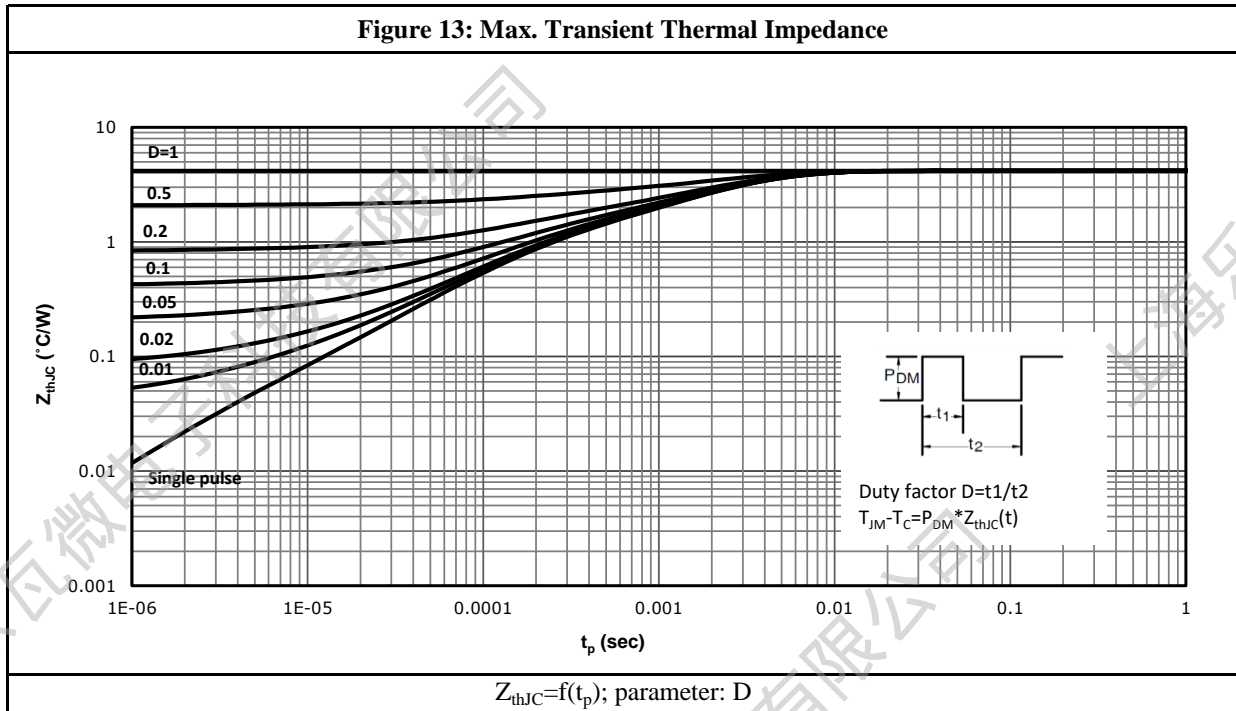
Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I_S	Diode Forward Current	$T_C = 25\text{ }^\circ\text{C}$	--	--	-12	A
V_{SD}	Diode Forward Voltage	$I_S = -2.0A, V_{GS} = 0V$	--	--	-1.2	V

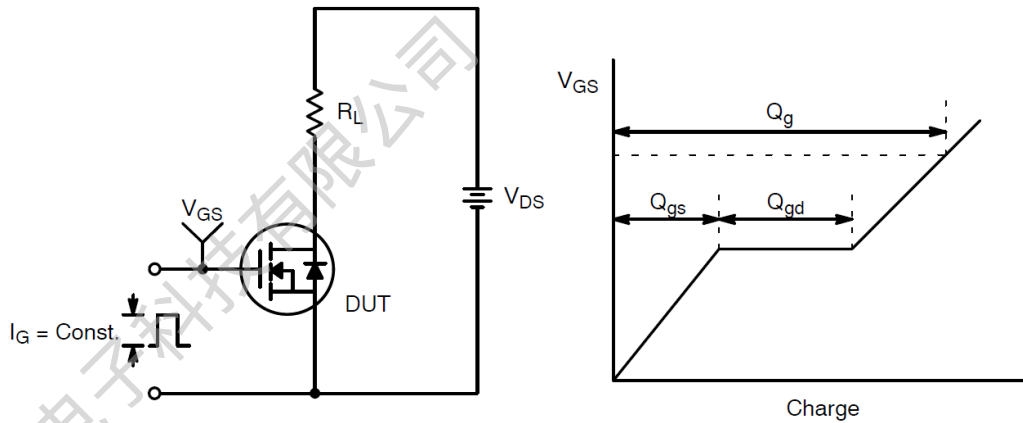
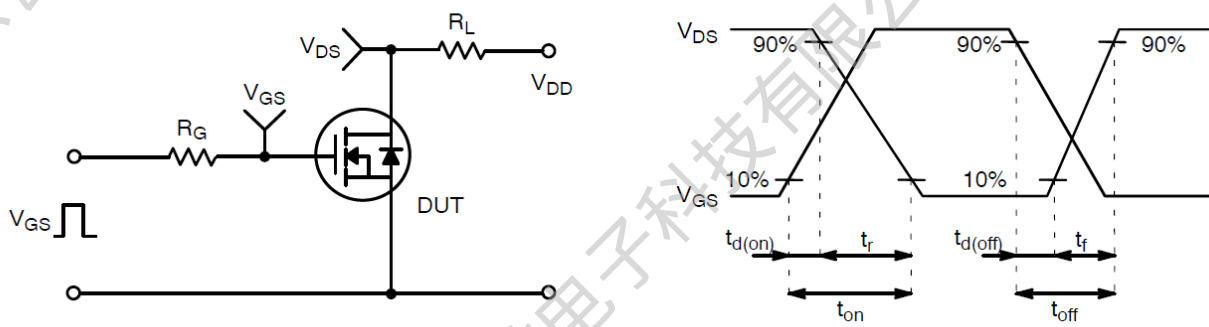
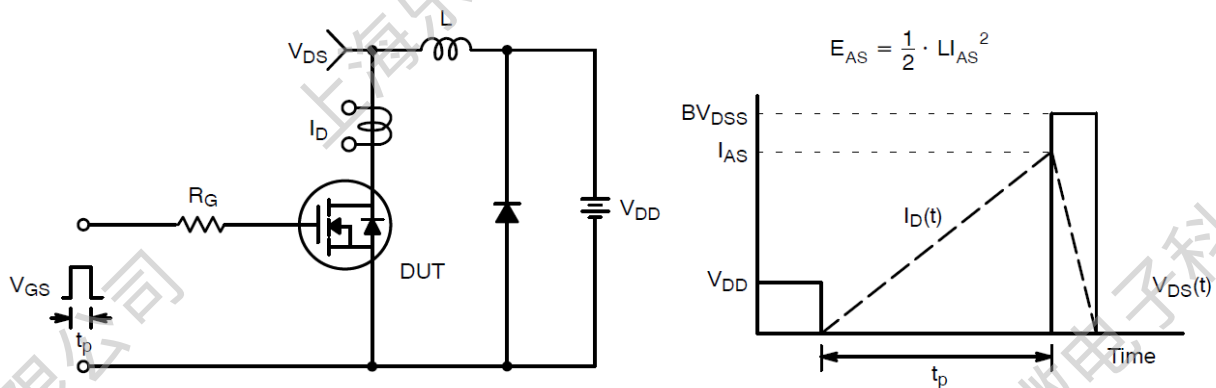
a1: Repetitive rating; pulse width limited by maximum junction temperature

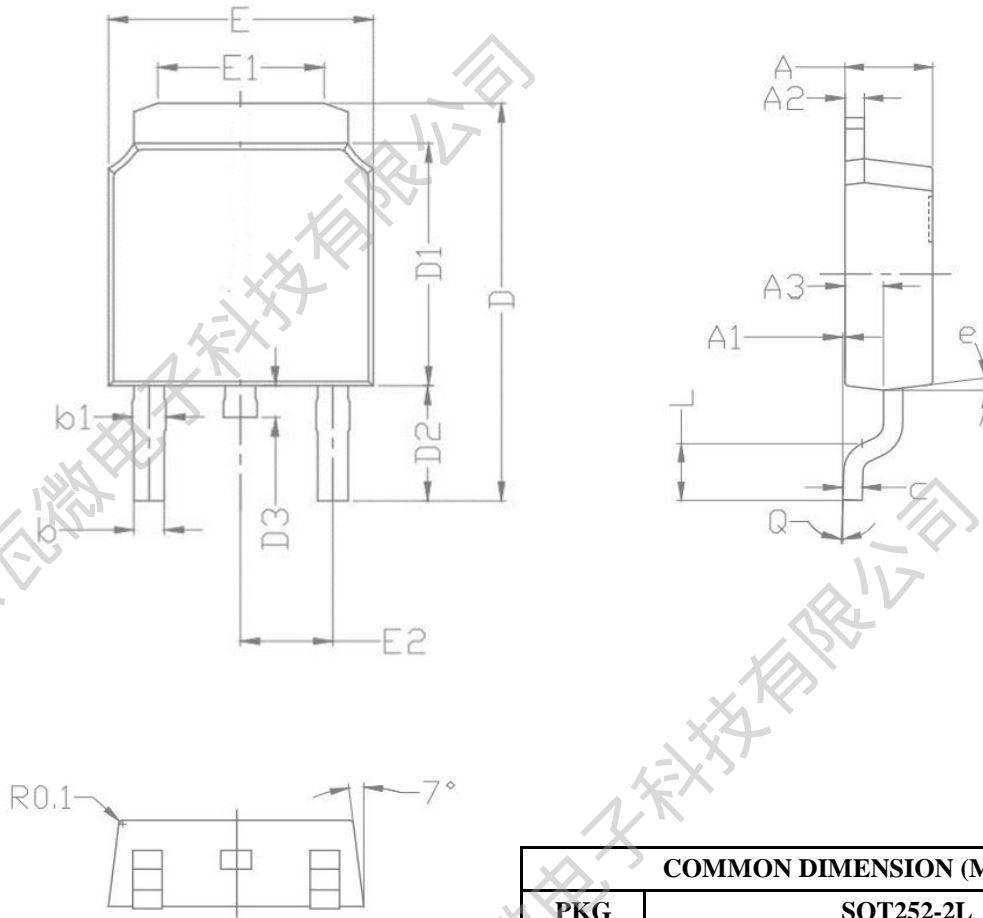
Characteristics Curve:








Test Circuit & Waveform:

Figure 14: Gate Charge Test Circuit & Waveform

Figure 15: Resistive Switching Test Circuit & Waveforms

Figure 16: Unclamped Inductive Switching Test Circuit & Waveforms

Package Outline:


COMMON DIMENSION (MM)			
PKG	SOT252-2L		
Symbol	MIN	NOM	MAX
A	2.200	2.300	2.400
A1	0.000	0.075	0.150
A2	0.500	0.508	0.550
A3	0.960	1.010	1.060
b	0.740	0.760	0.800
b1	0.880	0.900	0.950
C	0.500	0.508	0.550
D	9.800	10.025	10.350
D1	6.050	6.100	6.180
D2	2.850	2.900	2.950
D3	0.600	0.800	1.000
E	6.550	6.600	6.700
E1	4.050	4.130	4.200
E2	2.250	2.286	2.300
L	1.400	1.500	1.600
e	7.000		
Q	0°	2°	5°

Revision History:

Revison	Date	Descriptions
Rev 1.0	Feb.2024	Initial Version

Disclaimer:

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